

1 to 3 Cells Li-Ion Battery Protection IC for Secondary Protection

No. EA-416-210518

OUTLINE

The R5437L is an overcharge protection IC for 1 to 3 serial cells Li-ion / Li-polymer rechargeable battery. This device provides the high-accuracy voltage detection function and the shutdown function can reduce the supply current to the minimum when all cell's voltage becomes less than the shutdown detection voltage.

FEATURES

- High Voltage Tolerant Process
Absolute Maximum Ratings 26 V
- Low Supply Current
During Operation, Cell-voltage: 3.9 V, 3-Cells Typ. 0.85 μ A
- High-accuracy Voltage Detection
Overcharge Detector Threshold ($V_{DET1n}^{(1)}$) 4.10 V to 4.65 V, in 5 mV step
Overcharge Detector Threshold Accuracy ± 0.02 V ($T_a = 25^\circ\text{C}$)
 ± 0.025 V ($0^\circ\text{C} \leq T_a \leq 60^\circ\text{C}$)

Overcharge Release Voltage ($V_{REL1n}^{(1)}$) $V_{DET1n} - 0\text{V}$ to $V_{DET1n} - 0.5\text{V}$, in 50 mV step

Overcharge Detection Delay Time 2-, 4-, or 6-sec with Delay Time Shortening Function⁽²⁾
Overcharge Release Voltage Condition Voltage Release Type
- COUT Output (CMOS Output, Active-high) Typ. 4.7 V
- Shutdown Functions
Shutdown Detector Threshold Typ. 3.5 V ± 0.3 V
Shutdown Current Max. 0.1 μ A
- 1 to 3 Cells Selectable Battery Protection
- Compact Package
DFN 1814-6C 1.4mm x 1.8mm

APPLICATIONS

- Li-Ion or Li-Polymer Battery Protection

⁽¹⁾ V_{DET1n}, V_{REL1n} : $n = 1, 2, 3$

⁽²⁾ The delay time can be reduced down to approx. 1/90 by applying a 4 V ± 0.2 V to the VDD – VC1 pins.

SELECTION GUIDE

The overcharge and the delay time are user-selectable options.

Selection Guide

Product Name	Package	Quantity per Reel	Pb Free	Halogen Free
R5437Lxxx\$*-TR	DFN1814-6C	5,000 pcs	Yes	Yes

xxx: Specify the combination of the overcharge detector threshold (V_{DET1n}) and the overcharge release voltage (V_{REL1n})⁽¹⁾.

V_{DET1n} ⁽²⁾: 4.10 V to 4.65 V in 5 mV step

V_{REL1n} ⁽²⁾: $V_{DET1n} - 0$ V to $V_{DET1n} - 0.5$ V in 50 mV step

\$: Specify the combination of the overcharge detection delay time (t_{VDET1}) and the overcharge release delay time (t_{VREL1}). Refer to *Delay Time Code Table* for details.

Delay Time Code Table

Code	t_{VDET1} (s)	t_{VREL1} (ms)
A	2	16
B	4	16
C	6	16

*: Specify the function code.

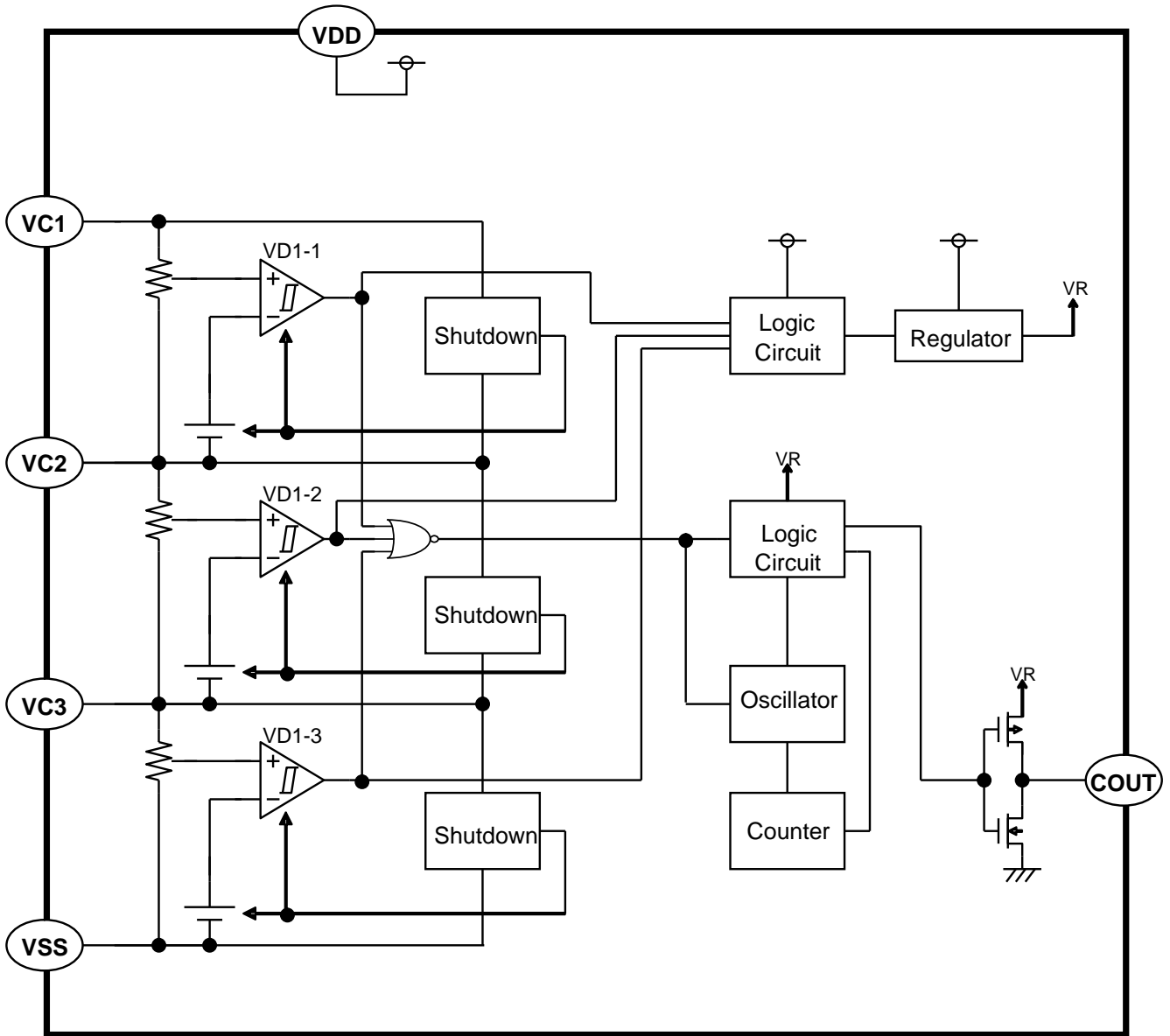
Function Code Table

Code	Overcharge Released Condition	COUT Output	
A	Voltage Release	CMOS	"H" Active

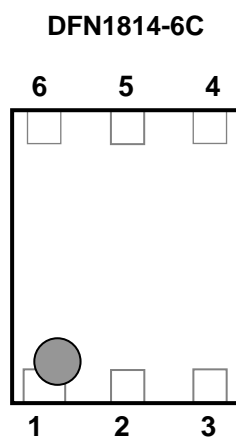
⁽¹⁾ Refer to *Product Code Table* for details.

⁽²⁾ V_{DET1n}, V_{REL1n} : $n = 1, 2, 3$

BLOCK DIAGRAM



R5437L Block Diagram

PIN DESCRIPTIONS**R5437L Pin Description**

Pin No.	Symbol	Description
1	VC1	CELL1 Plus Pin
2	VC2	CELL2 Plus Pin
3	VSS	IC Ground Pin
4	VC3	CELL3 Plus Pin
5	VDD	Power Supply Pin
6	COUT	Overcharge Detection Output Pin

ABSOLUTE MAXIMUM RATINGS

Absolute Maximum Ratings

(Ta = 25°C, V_{SS} = 0 V)

Symbol	Item	Rating	Unit
V _{DD}	Power Supply Voltage	V _{C1} -0.3 to V _{C1} +6.5	V
		V _{C1} -0.3 to 26	V
V _{C1}	CELL1 Plus Pin Input Voltage	V _{C2} -0.3 to V _{C2} +6.5	V
V _{C2}	CELL2 Plus Pin Input Voltage	V _{C3} -0.3 to V _{C3} +6.5	V
V _{C3}	CELL3 Plus Pin Input Voltage	-0.3 to 6.5	V
V _{COU} T	COU T Pin Output Voltage	-0.3 to V _{OH1} +0.3	V
P _D	Power Dissipation (Standard Land Pattern)	150	mW
T _j	Junction Temperature Range	-40 to 125	°C
T _{stg}	Storage Temperature Range	-55 to 125	°C

ABSOLUTE MAXIMUM RATINGS

Electronic and mechanical stress momentarily exceeded absolute maximum ratings may cause permanent damage and may degrade the lifetime and safety for both device and system using the device in the field. The functional operation at or over these absolute maximum ratings is not assured.

RECOMMENDED OPERATING CONDITION

Symbol	Item	Rating	Unit
V _{DD}	Operating Input Voltage	1.5 to 20 /	V
		V _{C1} +5 V	
T _a	Operating Temperature Range	-40 to 85	°C

RECOMMENDED OPERATING CONDITIONS

All of electronic equipment should be designed that the mounted semiconductor devices operate within the recommended operating conditions. The semiconductor devices cannot operate normally over the recommended operating conditions, even if they are used over such conditions by momentary electronic noise or surge. And the semiconductor devices may receive serious damage when they continue to operate over the recommended operating conditions.

ELECTRICAL CHARACTERISTICS

$V_{CELLn} = CELLn$ (Ex. V_{CELL1} is a voltage difference between VC1 and VC2)

$n = 1, 2, 3$, unless otherwise noted

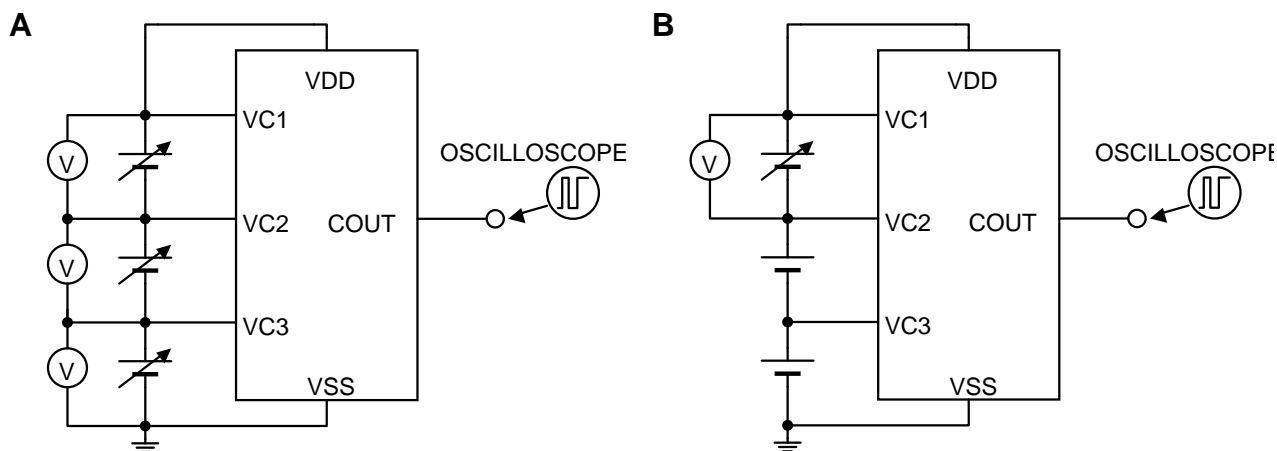
The specifications surrounded by are guaranteed by Design Engineering at $0^{\circ}\text{C} \leq T_a \leq 60^{\circ}\text{C}$.

R5437L Electrical Characteristics

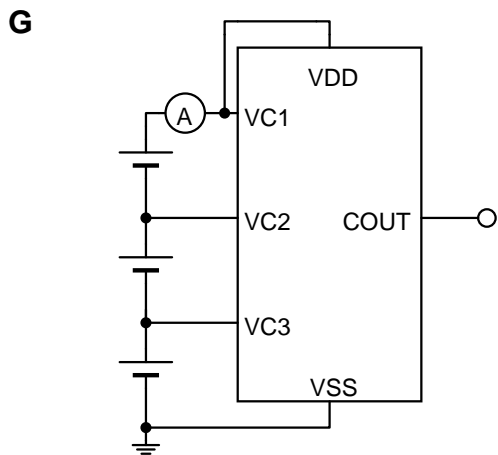
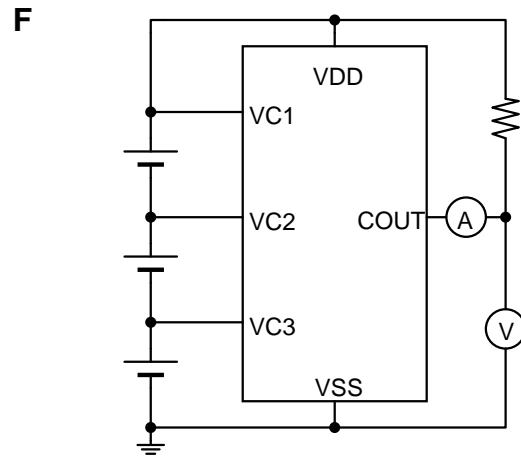
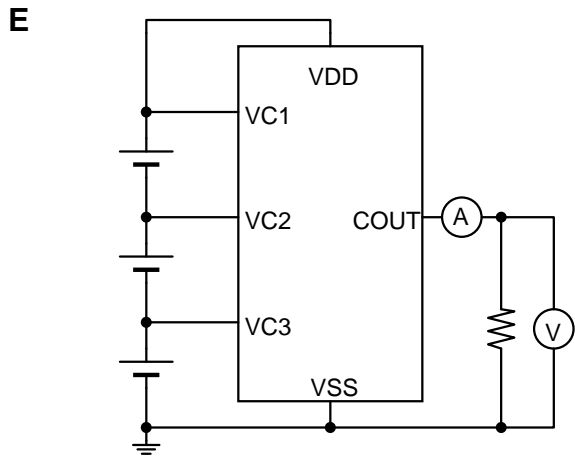
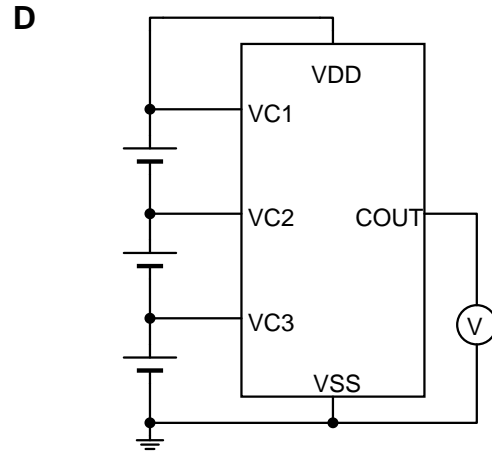
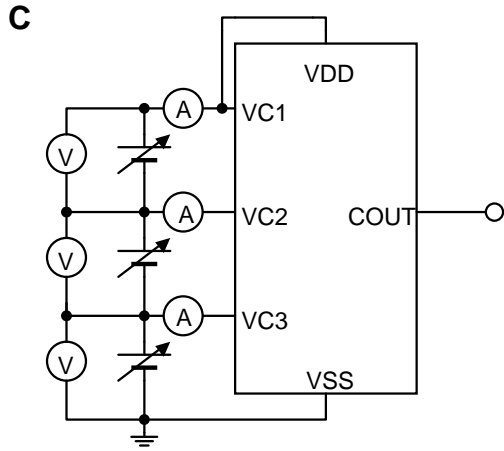
($T_a = 25^{\circ}\text{C}$)

Symbol	Item	Conditions	Min.	Typ.	Max.	Unit	Circuit (1)
V_{DET1n}	CELLn Overcharge Detection Voltage	Detect rising edge of supply voltage	V_{DET1n} -0.020V	V_{DET1n}	V_{DET1n} +0.020V	V	A
			V_{DET1n} -0.025V		V_{DET1n} +0.025V		
V_{REL1n}	CELLn Overcharge Release Voltage	Detect falling edge of supply voltage	V_{REL1n} -0.050V	V_{REL1n}	V_{REL1n} +0.050V	V	A
t_{VDET1}	Overcharge Detection Delay Time	$V_{CELLn}=3.9\text{ V}$ ($n=2,3$) $V_{CELL1}=3.9\text{ V} \rightarrow 4.7\text{ V}$	t_{VDET1} x 0.8	t_{VDET1}	t_{VDET1} x 1.2	s	B
t_{VREL1}	Overcharge Release Delay Time	$V_{CELLn}=3.9\text{ V}$ ($n=2,3$) $V_{CELL1}=4.7\text{ V} \rightarrow 3.9\text{ V}$	12.8	16	19.2	ms	B
V_{SHT}	Shutdown Detection Voltage	Detect falling edge of supply voltage	3.2	3.5	3.8	V	C
V_{OH1}	C _{OUT} Pch. ON Voltage 1	$I_{OH}=0\mu\text{A}, V_{CELLn} = 4.7\text{ V}$	4.0	4.7	5.4	V	D
		$I_{OH}=0\mu\text{A}, V_{CELLn} = 4.7\text{ V}$ ($n=1$, at 1 cell protection)		V_{DD}			
V_{OH2}	C _{OUT} Pch. ON Voltage 2	$I_{OH} = -50\mu\text{A},$ $V_{CELLn} = 4.7\text{V}$	V_{OH1} -0.5V	$V_{OH1}-0.1\text{V}$		V	E
V_{OL}	C _{OUT} Nch. ON Voltage	$I_{OL}=50\mu\text{A}, V_{CELLn}=3.9\text{ V}$		0.1	0.5	V	F
I_{SHT}	Shutdown Current	$V_{CELLn} = 3.1\text{ V}$			0.1	μA	G
I_{SS}	Supply Current	$V_{CELLn} = 3.9\text{ V}$		0.85	1.7	μA	G

TEST CIRCUITS



(1) Refer to *TEST CIRCUITS* for detail information.



THEORY OF OPERATION

Overcharge Detection Circuit, VD1-n (n = 1, 2, 3)

(See the following timing chart)

While the cells are charged, the voltage between VC1 pin and VC2 pin (Cell-1 voltage), the voltage between VC2 pin and VC3 pin (Cell-2 voltage), and the voltage between VC3 pin and VSS pin (Cell-3 voltage) are supervised. If at least one of the cells' voltage becomes equal or more than the overcharge detector threshold, the overcharge is detected, and an external charge control Nch. FET turns on with COUT pin being at "H" level and by cutting a fuse on the charger path, and charge stops.

To reset the overcharge and make the COUT pin level to "L" again after detecting over-charge, in such conditions that a time when all the cells' voltages are down to a level lower than overcharge released voltage. Internal fixed output delay times for overcharge detection and release from over-charge exist. Even if one of voltage of the cells keeps its level more than the overcharge detector threshold, and output delay time passes, overcharge voltage is detected. After detecting overcharge, even if all the cell voltages become equal or less than the released voltage from overcharge, if at least one of the cells voltage becomes higher than the released voltage from overcharge within the output delay time of the release from overcharge, then overcharge is not released.

The output type of the COUT pin is CMOS output between VSS and the built-in regulator, and "H" level of COUT pin is the output voltage of the built-in regulator.

Shutdown Function

The voltage between VC1 pin and VC2 pin (Cell-1 voltage), the voltage between VC2 pin and VC3 pin (Cell-2 voltage), and the voltage between VC3 pin and VSS pin (Cell-3 voltage) are supervised. If the cell voltage becomes equal or less than the shutdown detector threshold, the overcharge detector of the cell is halted, as a result, the consumption current of IC itself (Shutdown current) is extremely reduced. If at least one of the cells voltage becomes higher than the shutdown detection voltage, the shutdown detection is released.

Delay Shortening (DS) Function

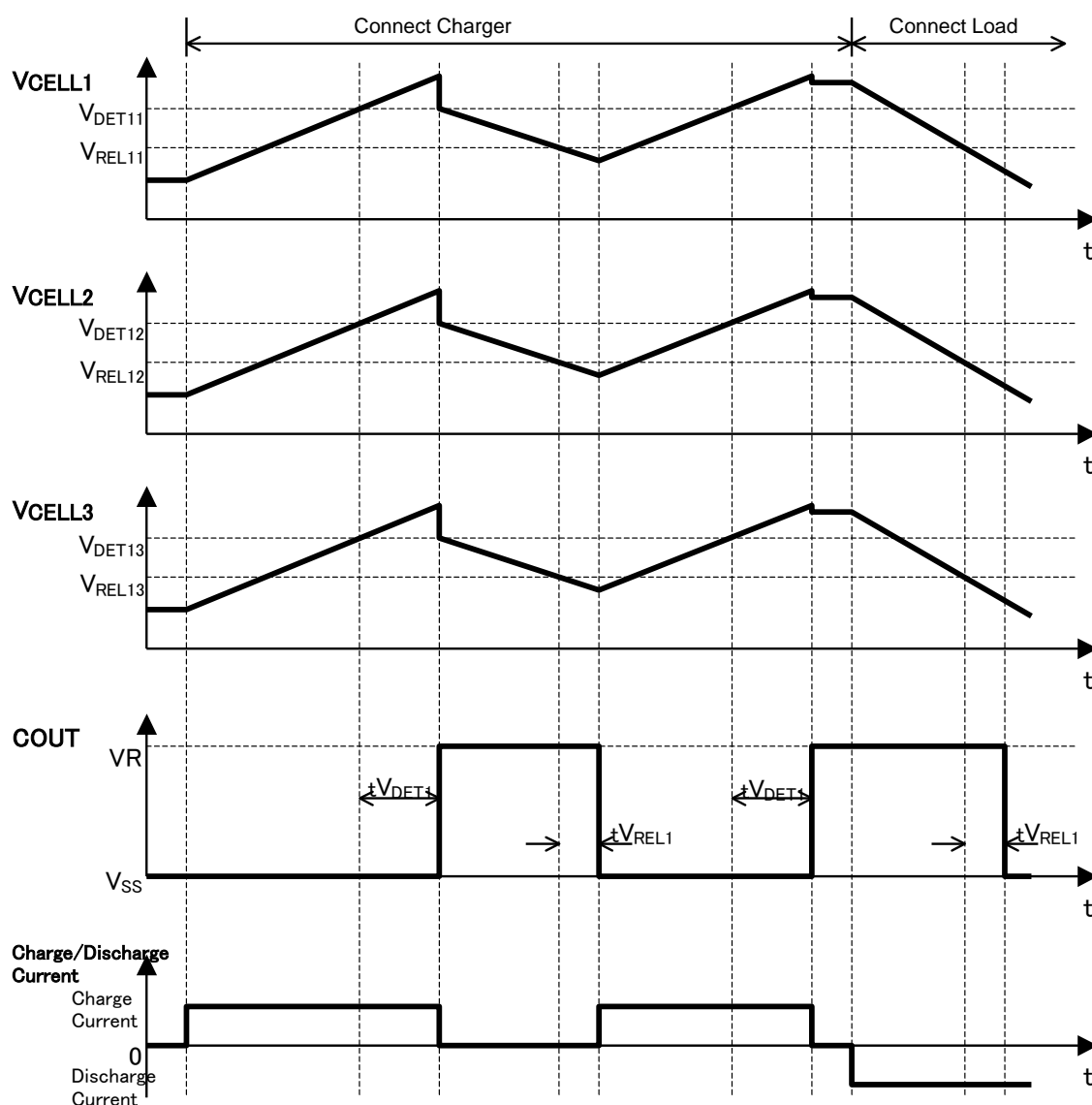
Applying a voltage of $4\text{ V} \pm 0.2\text{ V}$ between VDD and VC1 can shorten the overcharge detection delay time (t_{VDET1}) into approximately 1/90, likewise, the overcharge release delay time (t_{VREL1}) into approximately 1/60.

1-cell/ 2-cell Protection Alternative

By short-circuiting between cells, this device can meet as a protection IC for 1 or 3 cells placed in series. The following table indicates pins to short-circuit depending on protected cells.

Protected Cells	Pins to short-circuit
1-cell protection	VC1 and VC2 pins, and VC3 and VSS pins
2-cell protection	VC1 and VC2 pins, or VC3 and VSS pins

If providing other connections except above short-circuit for 1 or 2 cells protection, perform thorough evaluation using the actual devices.

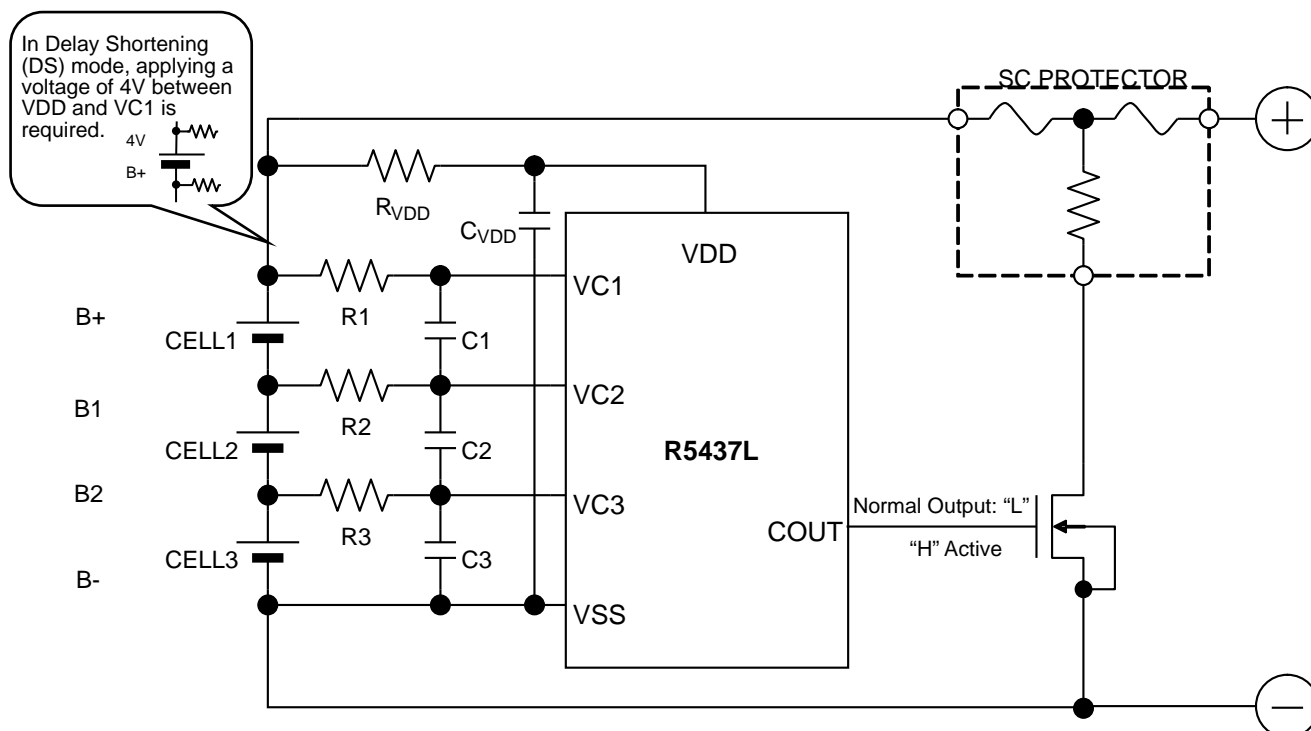


Overcharge Operation Timing Chart

APPLICATION INFORMATION

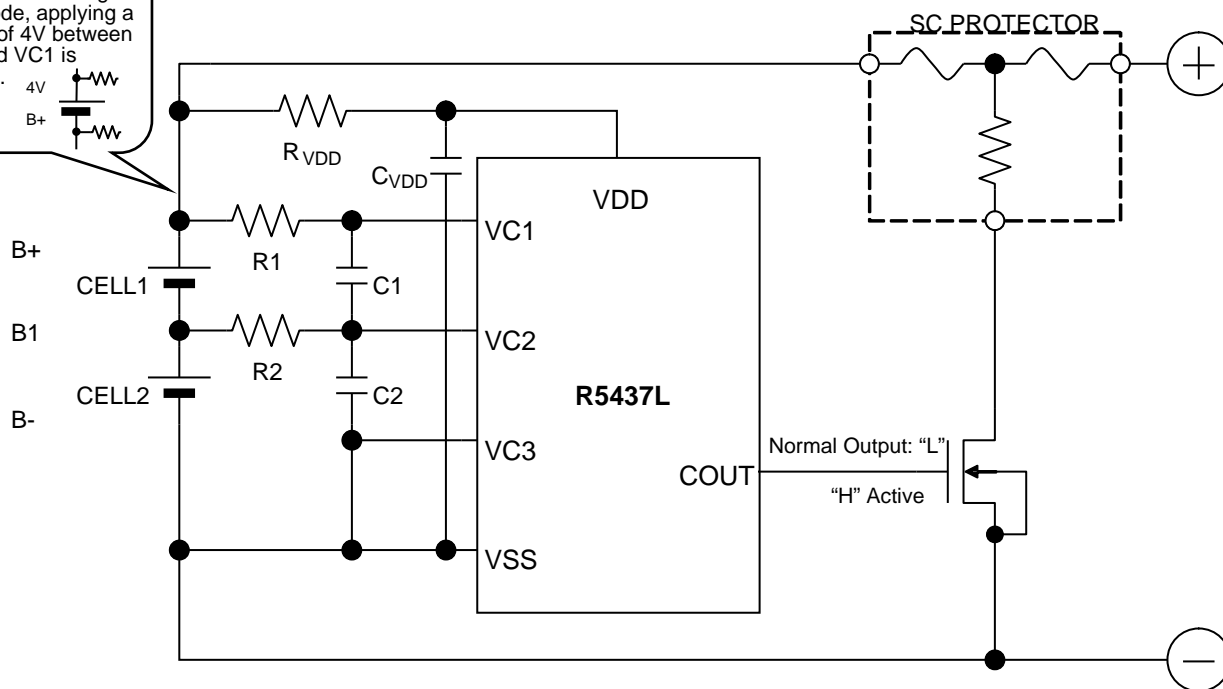
Typical Application Circuits in Normal Mode (CMOS Output, Active-high)

As for the order of cell's connection, connect a positive terminal of CELL1 as the end terminal. If connected another terminal, a fuse blowout might be caused by transiently "High" output of the COUT pin.



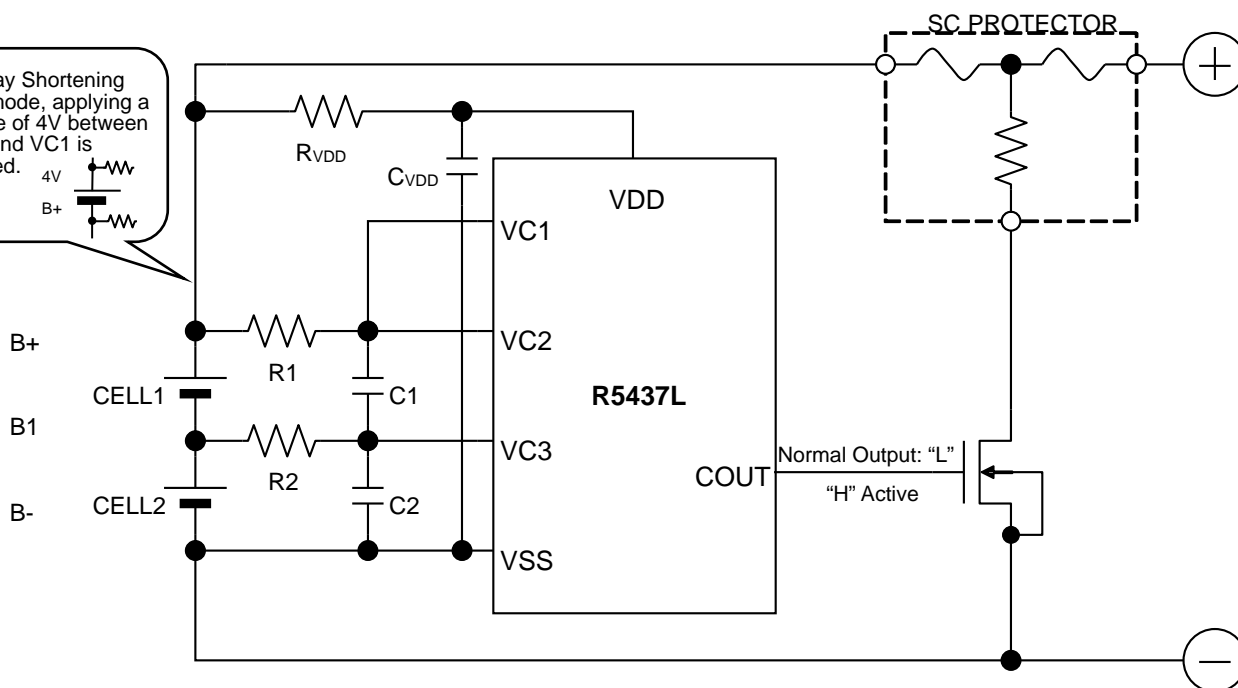
Typical Application Circuit for 3-cell Protection

In Delay Shortening (DS) mode, applying a voltage of 4V between VDD and VC1 is required.

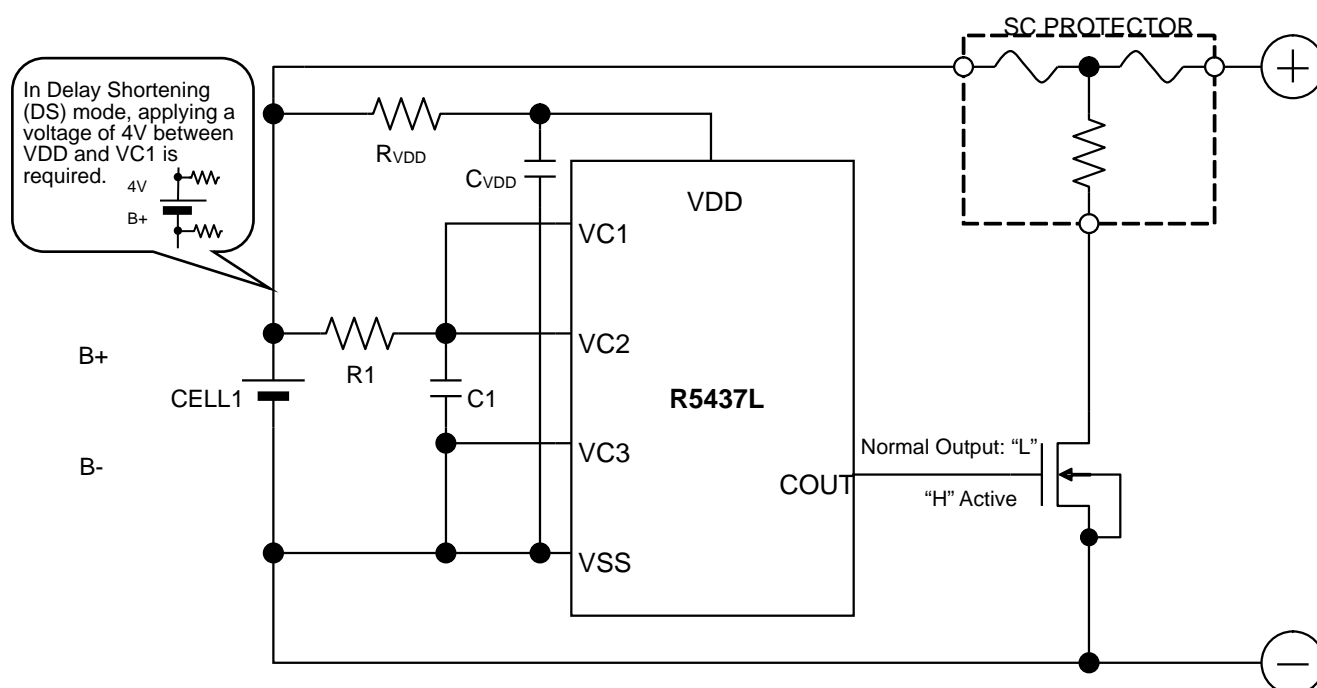


Typical Application Circuit for 2-cell Protection -1

In Delay Shortening (DS) mode, applying a voltage of 4V between VDD and VC1 is required.



Typical Application Circuit for 2-cell Protection -2



Typical Application Circuit for 1-cell Protection

External Components

Symbol	Typ.	Unit	Range
R _{VDD}	100	Ω	100 to 1000
R ₁	1000	Ω	330 to 1000
R ₂	1000	Ω	330 to 1000
R ₃	1000	Ω	330 to 1000
C _{VDD}	0.1	μF	0.01 to 1
C ₁	0.1	μF	0.01 to 1
C ₂	0.1	μF	0.01 to 1
C ₃	0.1	μF	0.01 to 1

Technical Notes on the Selection Components

- The voltage fluctuation is stabilized with R_{VDD} and C_{VDD} . If a small R_{VDD} is set, in the case of the large transient may happen to the cell voltage, by the flowing current, the IC may be unstable. If a large R_{VDD} is set, by the consumption current of the IC itself, the voltage difference between VDD pin and VC1 pin is generated, and unexpected operation may result. Therefore, the appropriate value range of R_{VDD} is from 100 Ω to 1 k Ω . To make a stable operation of the IC, the appropriate value range of C_{VDD} is from 0.01 μ F to 1.0 μ F.
- The voltage fluctuation is stabilized with R1 to R3 and C1 to C3. If a R1 to R3 is too large, by the conduction current at detection, the detector threshold may shift higher. Therefore, the appropriate value range of R1 to R3 is equal or less than 1 k Ω . To make a stable operation of the IC, the appropriate value range of C1 to C3 is 0.01 μ F or more.
- The typical application circuit diagrams are just examples. This circuit performance largely depends on the PCB layout and external components. In the actual application, fully evaluation is necessary.
- Overvoltage and the over current beyond the absolute maximum rating should not be forced to the protection IC and external components. During the time until the fuse is open after detecting overcharge, a large current may flow through the FET. Select an FET with large enough current capacity in order to endure the large current.
- To connect the SC protector, connect the SC protector to the cell must be the last.

Contact Information for Inquiries regarding SC PROTECTOR

Dexerials Corporation (Sony Chemical & Information Device Company Ltd.)

Gate-city Osaki East Tower 8F, 1-11-2 Osaki, Shinagawa, Tokyo, 141-0032

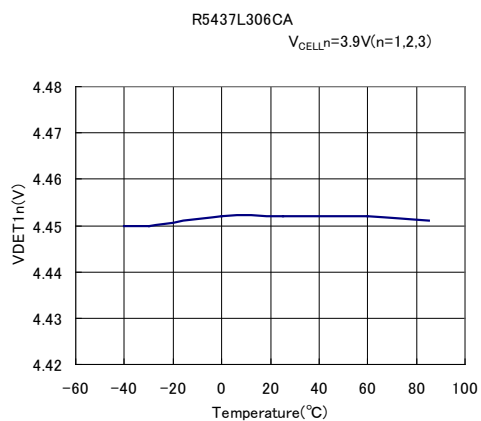
TEL: 03-5435-3946

URL: <http://www.dexerials.jp>

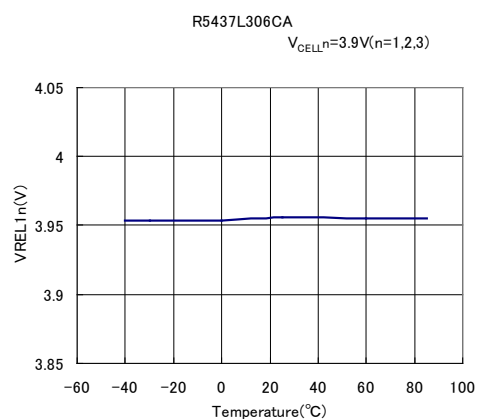
TYPICAL CHARACTERISTICS

Part1. vs. Temperature

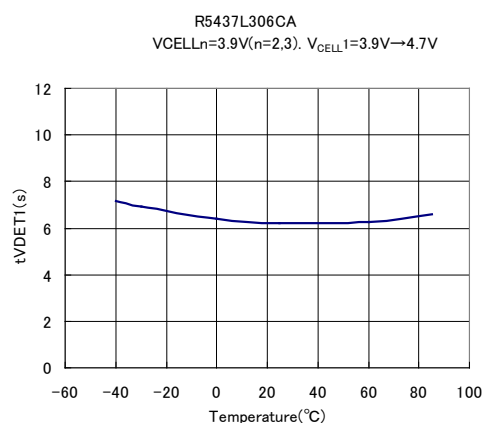
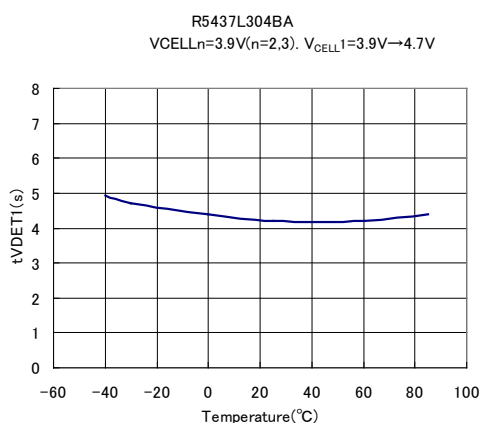
1) CellIn Overcharge Detection Threshold vs. Temperature



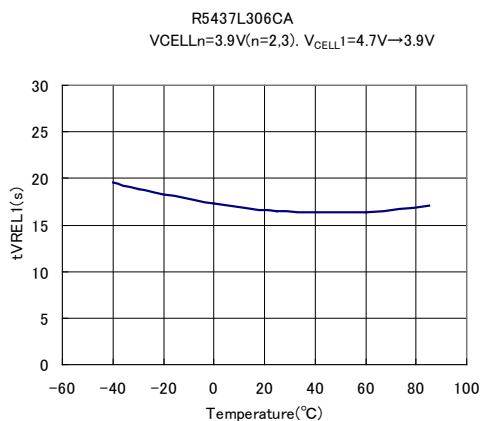
2) CellIn Overcharge Release Voltage vs. Temperature



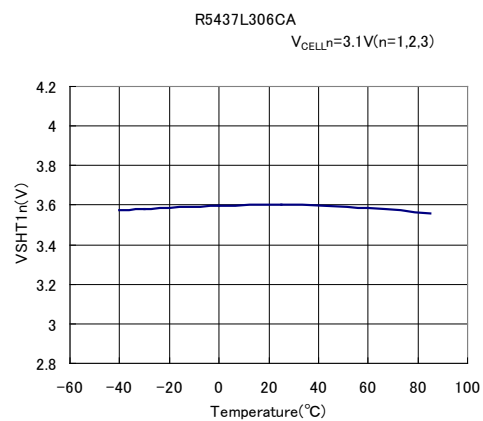
3) Overcharge Output delay Time vs. Temperature



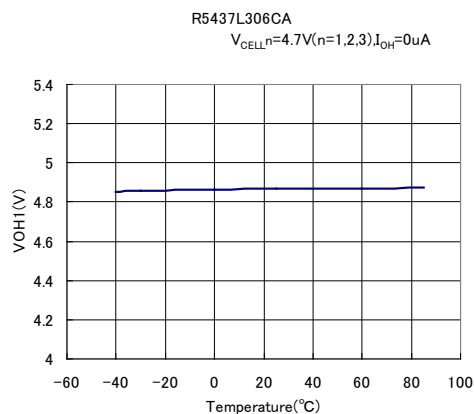
4) Released Delay Time from Overcharge vs. Temperature



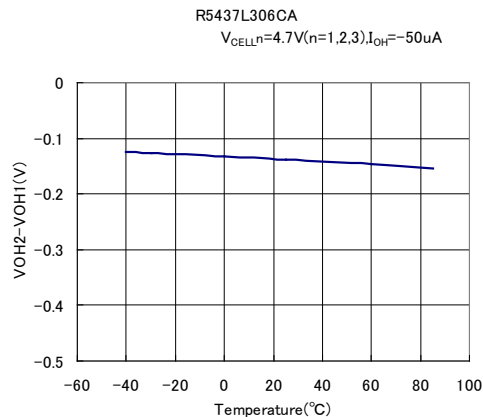
5) CellIn Shutdown Threshold vs. Temperature



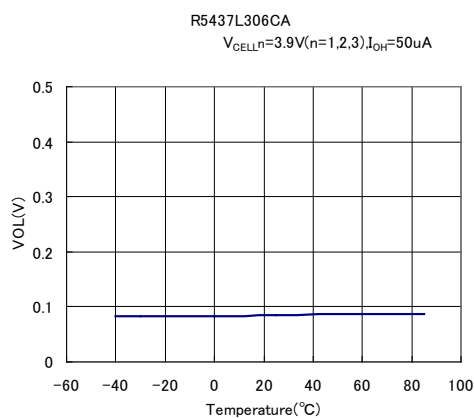
6) COUT Pch. On Voltage (No Load) vs. Temperature



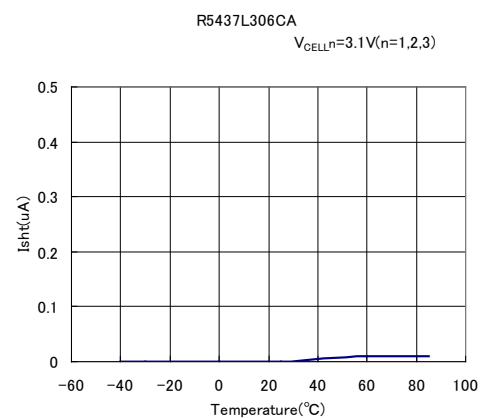
7) COUT Pch. On Voltage vs. Temperature



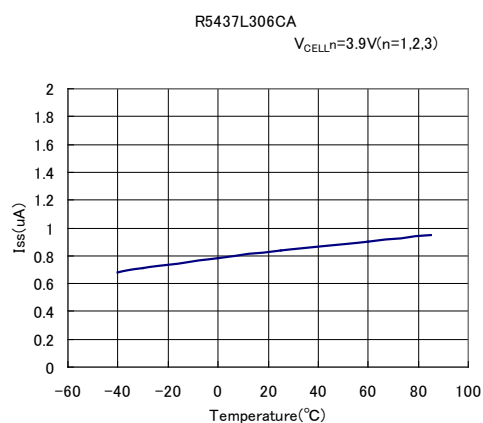
8) COUT Nch. On Voltage vs. Temperature



9) Shutdown Current vs. Temperature

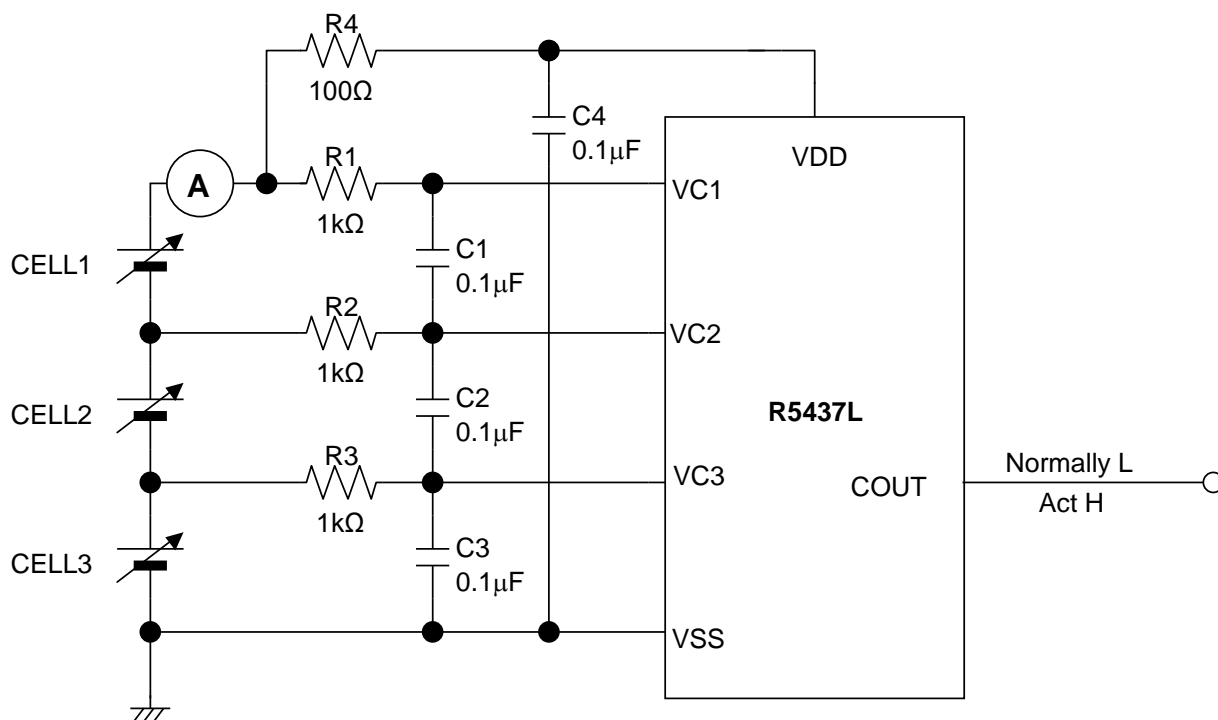
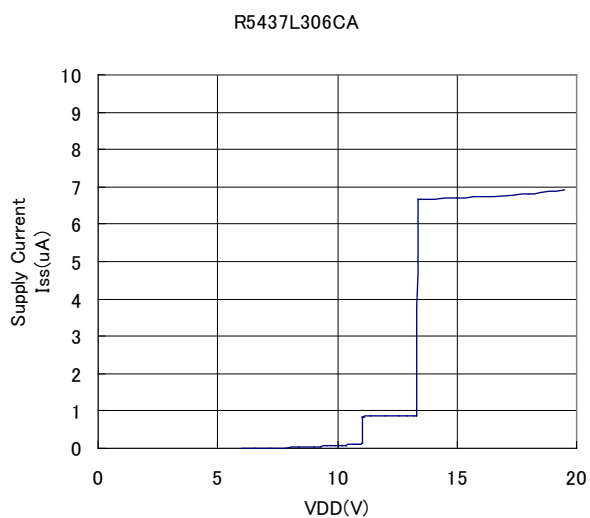


10) Supply Current vs. Temperature



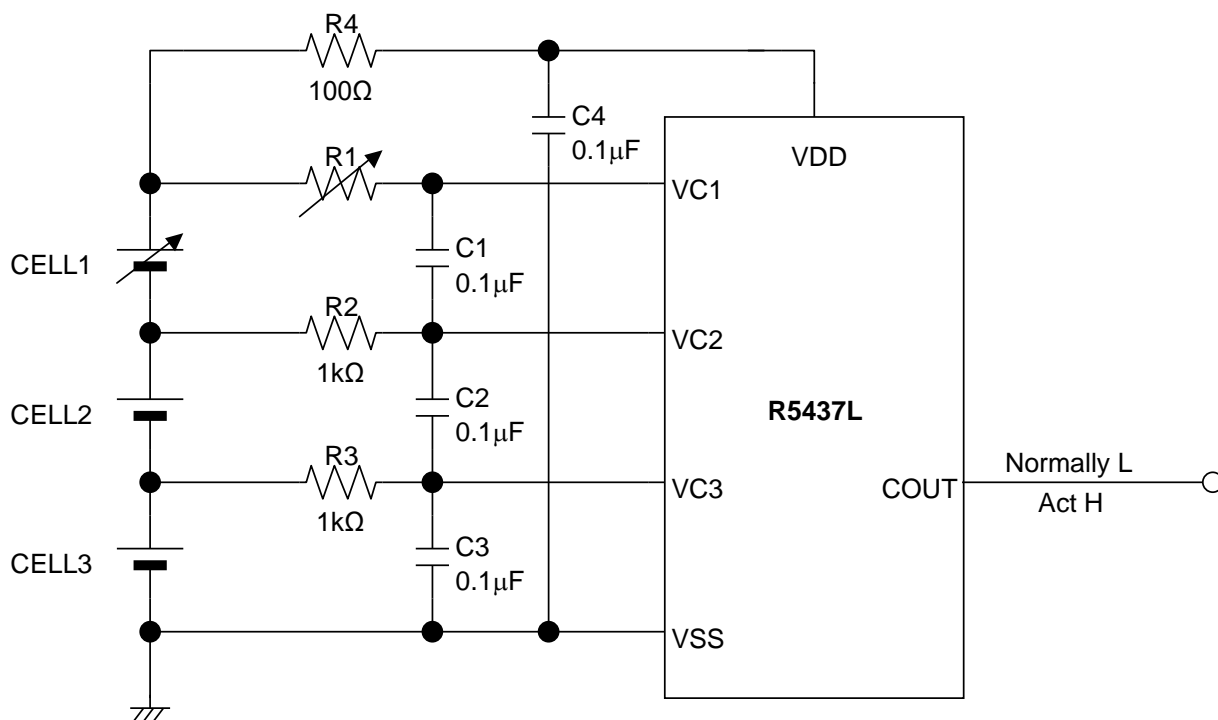
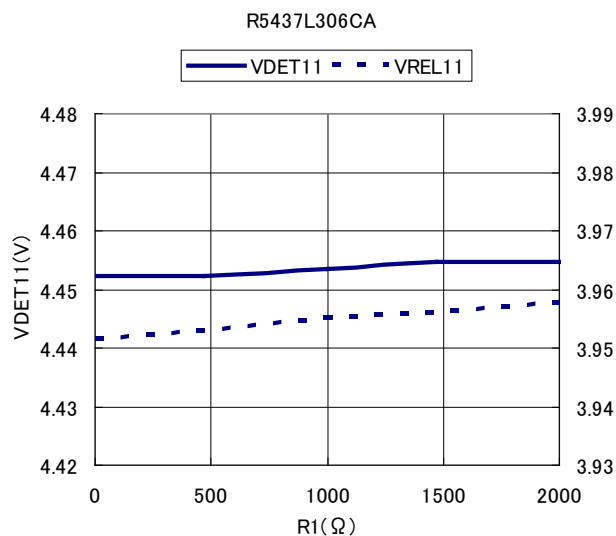
Part2. Supply Current vs. VDD (R5437L306CA)

3-cell Protection Supply Current vs. VDD

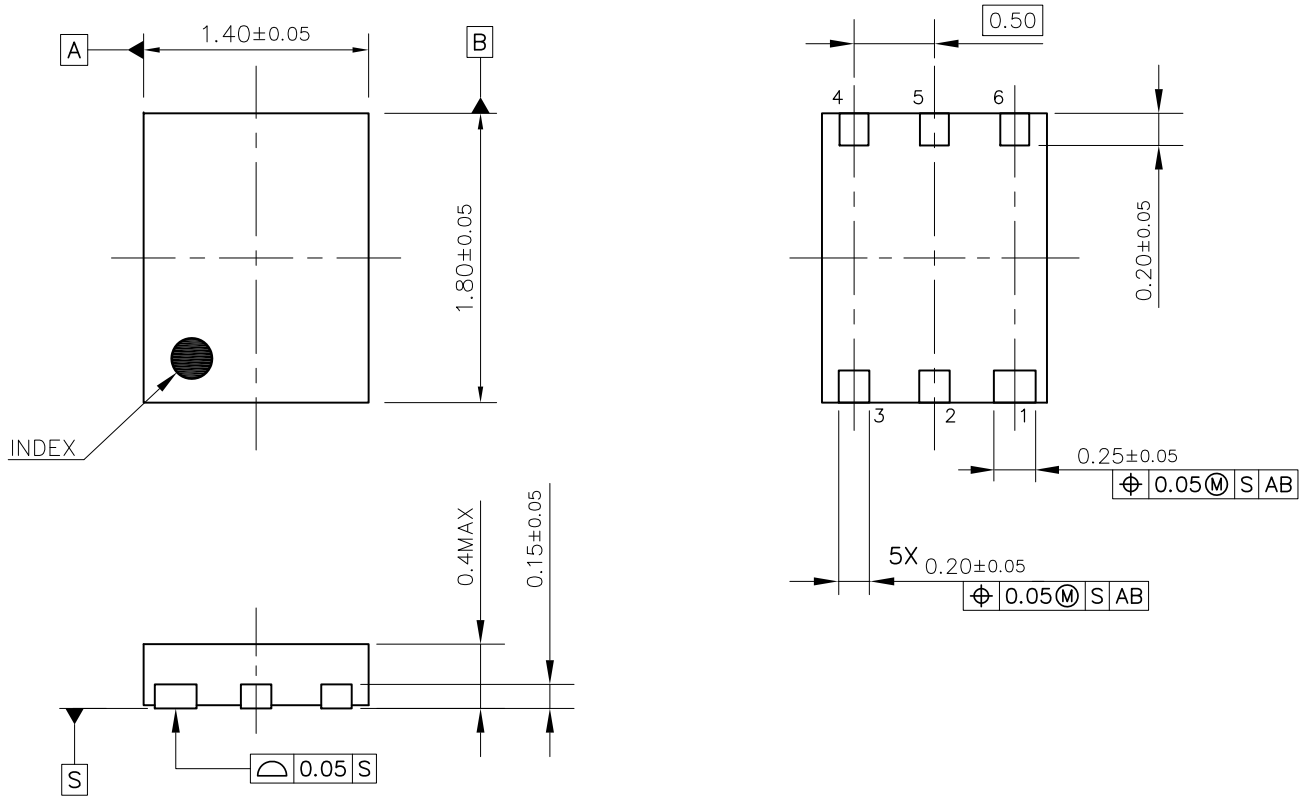


Test Circuit

Part3. vs. External Resister Dependence (R5437L306CA)
Overcharge Detection Voltage / Overcharge Release Voltage vs. R1



Test Circuit



DFN1814-6C Package Dimensions (Unit: mm)



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